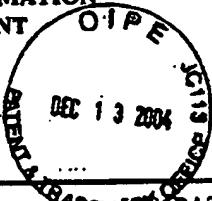


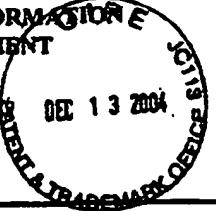
FORM PTO-1449		ATTY DOCKET NO.: ASC-23DVC2	
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		APPLICANT(S):	Fitzgerald
		SERIAL NO.:	10/022,689
		FILING DATE:	December 17, 2001
		GROUP:	2813

PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>Re</i>	A121	4,969,031	11/06/1990	Kobayashi <i>et al.</i>		—	—
<i>Re</i>	A122	5,240,876	08/31/1993	Gaul <i>et al.</i>		—	—
<i>Re</i>	A123	5,548,128	08/20/1996	Soref <i>et al.</i>		—	—
<i>Re</i>	A124	5,572,043	11/05/1996	Shimizu <i>et al.</i>		—	—
<i>Re</i>	A125	5,607,876	03/04/1997	Biegelsen <i>et al.</i>		—	—
<i>Re</i>	A126	6,352,909	03/05/2002	Usenko		—	03/26/2000
<i>Re</i>	A127	6,372,593	04/16/2002	Hattori <i>et al.</i>		—	07/19/2000
<i>Re</i>	A128	6,489,639	12/03/2002	Hoke <i>et al.</i>		—	05/24/2000
<i>Re</i>	A129	6,524,935	02/25/2003	Canapari <i>et al.</i>		—	09/29/2000
<i>Re</i>	A130	6,646,322	11/11/2003	Fitzgerald		—	07/16/2001
<i>Re</i>	A131	6,677,192	01/13/2004	Fitzgerald		—	07/16/2001
<i>Re</i>	A132	6,703,688	03/09/2004	Fitzgerald		—	07/16/2001
<i>Re</i>	A133	6,750,130	06/15/2004	Fitzgerald		—	01/07/2001

FOREIGN PATENT DOCUMENTS									
EXAM. INIT.	DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)	
<i>Re</i>	B40	61-141116	06/28/1986	JP	—	—		Y (abstract only)	
<i>Re</i>	B41	2-210816	08/22/1990	JP	—	—		Y (abstract only)	
<i>Re</i>	B42	3-036717	02/18/1991	JP	—	—		Y	

OTHER ART, JOURNAL ARTICLES										
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)									
<i>Re</i>	C95	Godbey <i>et al.</i> , (1990) "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained Si _{0.7} Ge _{0.3} Layer as an Etch Stop," <i>Journal of the Electrical Society</i> , Vol. 137, No. 10 (October 1990) pp. 3219-3223.								
<i>Re</i>	C96	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in (Al _x Ga _{1-x}) _{As} In _{0.5} P heterostructures," <i>Journal of Applied Physics</i> , Vol. 91, No. 8 (2002), pp. 4891-4899.								

EXAMINER *hannah S* DATE CONSIDERED *3/3/05*

449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		ATTY DOCKET NO.: ASC-23DVC2						
		APPLICANT(S): Fitzgerald						
		SERIAL NO.: 10/022,689						
		FILING DATE: December 17, 2001						
		GROUP: 2813						
U.S. PATENT DOCUMENTS								
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS								
EXAM. INIT.	DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES								
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)							
<i>Ab</i>	C97	Halsall <i>et al.</i> , "Electron diffraction and Raman studies of the effect of substrate misorientation on ordering in the AlGaN/P system," <i>Journal of Applied Physics</i> , Vol. 85, No. 1 (1999), pp. 199-202.						
<i>Ab</i>	C98	Hsu <i>et al.</i> , "Surface morphology of related Ge _x Si _{1-x} films," <i>Appl. Phys. Lett.</i> , Vol. 61, No. 11 (1992), pp. 1293-1295.						
<i>Ab</i>	C99	Huang <i>et al.</i> , (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", <i>2001 Symposium on VLSI Technology, Digest of Technical Papers</i> , pages 57-58						
<i>Ab</i>	C100	Langdo <i>et al.</i> , (2002) "Preparation of Novel SiGe-free Strained Si on Insulator Substrates" <i>IEEE International SOI Conference</i> , pages 211-212 (XP002263057)						
EXAMINER: <i>Hassia Schulte</i>				DATE CONSIDERED: 3/3/05				

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